

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
Euijoon Yoon et al.

Application No.: 10/563,854

Confirmation No.: 3828

Filed: June 9, 2006

Art Unit: 2823

For: GROWTH METHOD OF NITRIDE
SEMICONDUCTOR EPITAXIAL LAYERS

Examiner: Maldonado, Julio J.

DO NOT ENTER: /J.M./

AMENDMENT AFTER FINAL ACTION (37 C.F.R. SECTION 1.116)

February 8, 2010

MS AF
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

INTRODUCTORY COMMENTS

In response to the Final Office Action dated December 8, 2009, and with the Examiner's approval, please amend the above-identified U.S. patent application as follows:

Amendments to the Claims are reflected in the listing of claims which begins on page 2 of this paper.

Remarks/Arguments begin on page 8 of this paper.